

MC74VHC86

Quad 2-Input XOR Gate

The MC74VHC86 is an advanced high speed CMOS 2-input Exclusive-OR gate fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The internal circuit is composed of three stages, including a buffer output which provides high noise immunity and stable output. The inputs tolerate voltages up to 7 V, allowing the interface of 5 V systems to 3 V systems.

Features

- High Speed: $t_{PD} = 4.8 \text{ ns}$ (Typ) at $V_{CC} = 5 \text{ V}$
- Low Power Dissipation: $I_{CC} = 2 \mu\text{A}$ (Max) at $T_A = 25^\circ\text{C}$
- High Noise Immunity: $V_{NIH} = V_{NIL} = 28\% V_{CC}$
- Power Down Protection Provided on Inputs
- Balanced Propagation Delays
- Designed for 2 V to 5.5 V Operating Range
- Low Noise: $V_{OLP} = 0.8 \text{ V}$ (Max)
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance: Human Body Model (HBM) > 2000 V; Machine Model > 200 V
- Chip Complexity: 56 FETs or 14 Equivalent Gates
- These Devices are Pb-Free and are RoHS Compliant

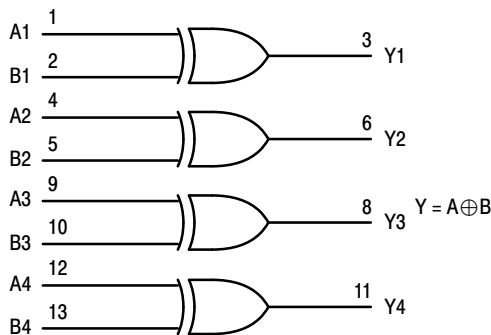


Figure 1. Logic Diagram

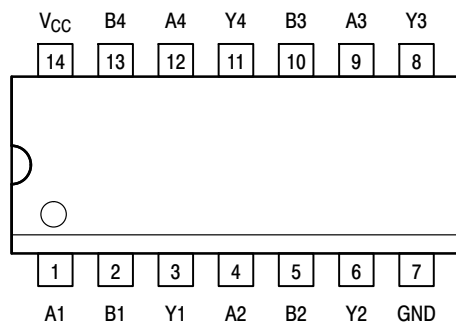


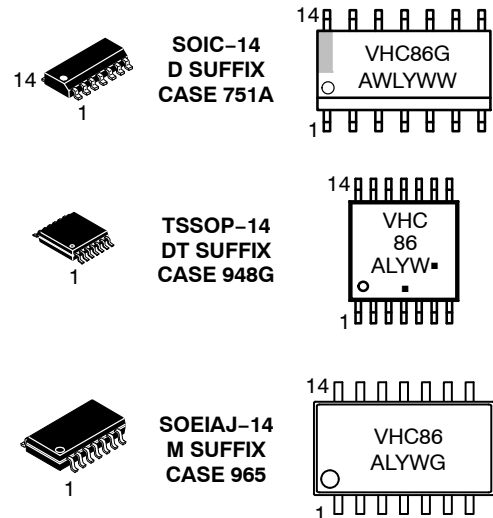
Figure 2. Pinout: 14-Lead Packages (Top View)



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MARKING DIAGRAMS



A = Assembly Location
 WL, L = Wafer Lot
 Y, YY = Year
 WW, W = Work Week
 G or ■ = Pb-Free Package
 (Note: Microdot may be in either location)

FUNCTION TABLE

Inputs		Output
A	B	Y
L	L	L
L	H	H
H	L	H
H	H	L

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

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MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	DC Supply Voltage	-0.5 to +7.0	V
V_{in}	DC Input Voltage	-0.5 to +7.0	V
V_{out}	DC Output Voltage	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	Input Diode Current	-20	mA
I_{OK}	Output Diode Current	± 20	mA
I_{out}	DC Output Current, per Pin	± 25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins	± 50	mA
P_D	Power Dissipation in Still Air, SOIC Packages [†] TSSOP Package [†]	500 450	mW
T_{stg}	Storage Temperature	-65 to +150	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $GND \leq (V_{in} \text{ or } V_{out}) \leq V_{CC}$. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

[†]Derating SOIC Packages: - 7 mW/°C from 65° to 125°C
TSSOP Package: - 6.1 mW/°C from 65° to 125°C

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V_{CC}	DC Supply Voltage	2.0	5.5	V
V_{in}	DC Input Voltage	0	5.5	V
V_{out}	DC Output Voltage	0	V_{CC}	V
T_A	Operating Temperature, All Package Types	-55	+125	°C
t_r, t_f	Input Rise and Fall Time $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0	100 20	ns/V

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DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V _{CC} V	T _A = 25°C			T _A = -55°C to +125°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	High-Level Input Voltage		2.0 3.0 to 5.5	1.50 V _{CC} × 0.7			1.50 V _{CC} × 0.7		V
V _{IL}	Low-Level Input Voltage		2.0 3.0 to 5.5			0.50 V _{CC} × 0.3		0.50 V _{CC} × 0.3	V
V _{OH}	High-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{OH} = -50 μA	2.0 3.0 4.5	1.9 2.9 4.4	2.0 3.0 4.5		1.9 2.9 4.4		V
		V _{in} = V _{IH} or V _{IL} I _{OH} = -4 mA I _{OH} = -8 mA	3.0 4.5	2.58 3.94			2.48 3.80		
V _{OL}	Low-Level Output Voltage	V _{in} = V _{IH} or V _{IL} I _{OL} = 50 μA	2.0 3.0 4.5		0 0 0	0.1 0.1 0.1		0.1 0.1 0.1	V
		V _{in} = V _{IH} or V _{IL} I _{OL} = 4 mA I _{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44	
I _{in}	Input Leakage Current	V _{in} = 5.5 V or GND	0 to 5.5			±0.1		±1.0	μA
I _{CC}	Quiescent Supply Current	V _{in} = V _{CC} or GND	5.5			2.0		20.0	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

Symbol	Parameter	Test Conditions	T _A = 25°C			T _A = -55°C to +125°C		Unit
			Min	Typ	Max	Min	Max	
t _{PLH} , t _{PHL}	Propagation Delay, A or B to Y	V _{CC} = 3.3 ± 0.3 V C _L = 15 pF C _L = 50 pF		7.0 9.5	11.0 14.5	1.0 1.0	13.0 16.5	ns
		V _{CC} = 5.0 ± 0.5 V C _L = 15 pF C _L = 50 pF		4.8 6.3	6.8 8.8	1.0 1.0	8.0 10.0	
C _{in}	Input Capacitance			4	10		10	pF

C _{PD}	Power Dissipation Capacitance (Note 1.)	Typical @ 25°C, V _{CC} = 5.0 V		pF
		18		

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}/4 (per gate). C_{PD} is used to determine the no-load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.

NOISE CHARACTERISTICS (Input t_r = t_f = 3.0ns, C_L = 50 pF, V_{CC} = 5.0 V, Measured in SOIC Package)

Symbol	Characteristic	T _A = 25°C		Unit
		Typ	Max	
V _{OLP}	Quiet Output Maximum Dynamic V _{OL}	0.3	0.8	V
V _{OLV}	Quiet Output Minimum Dynamic V _{OL}	-0.3	-0.8	V
V _{IHD}	Minimum High Level Dynamic Input Voltage		3.5	V
V _{ILD}	Maximum Low Level Dynamic Input Voltage		1.5	V

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ORDERING INFORMATION

Device	Package	Shipping†
MC74VHC86DR2G	SOIC-14 (Pb-Free)	2500 Tape & Reel
MC74VHC86DTG	TSSOP-14 (Pb-Free)	96 Units / Rail
MC74VHC86DTR2G	TSSOP-14 (Pb-Free)	2500 Tape & Reel
MC74VHC86MELG	SOEIAJ-14 (Pb-Free)	2000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

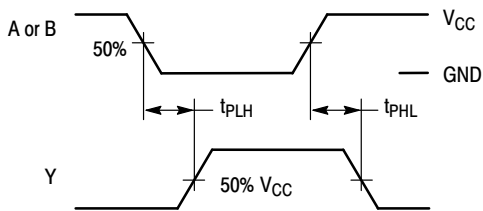
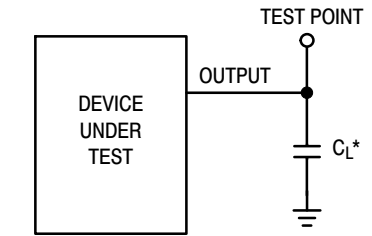


Figure 3. Switching Waveforms



*Includes all probe and jig capacitance

Figure 4. Test Circuit

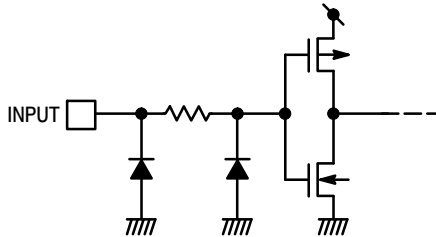
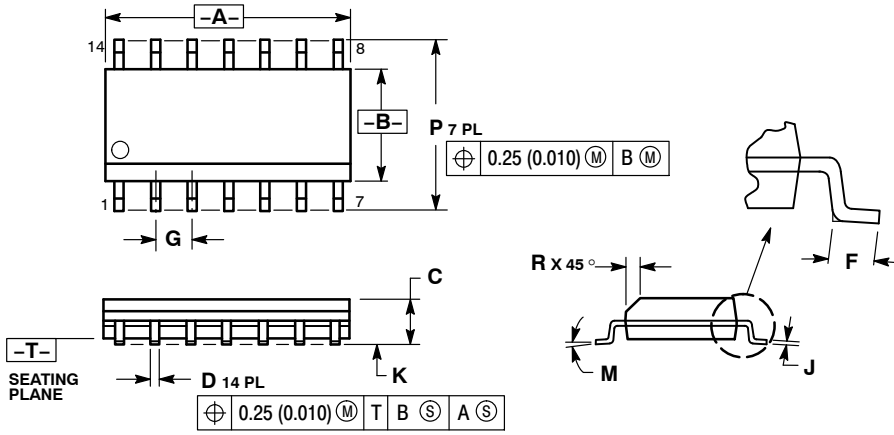


Figure 5. Input Equivalent Circuit

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PACKAGE DIMENSIONS

SOIC-14
CASE 751A-03
ISSUE J

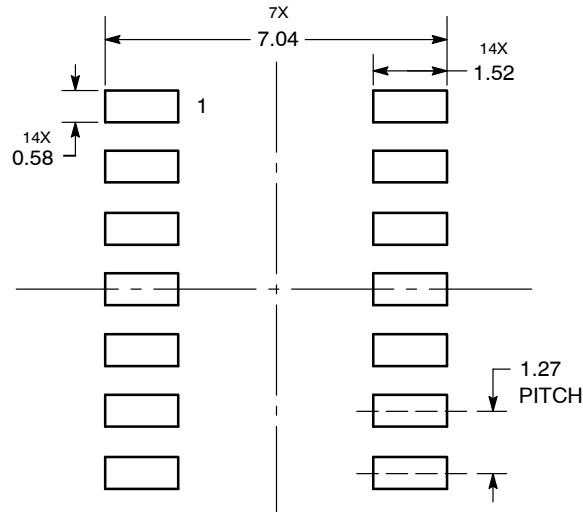


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT*



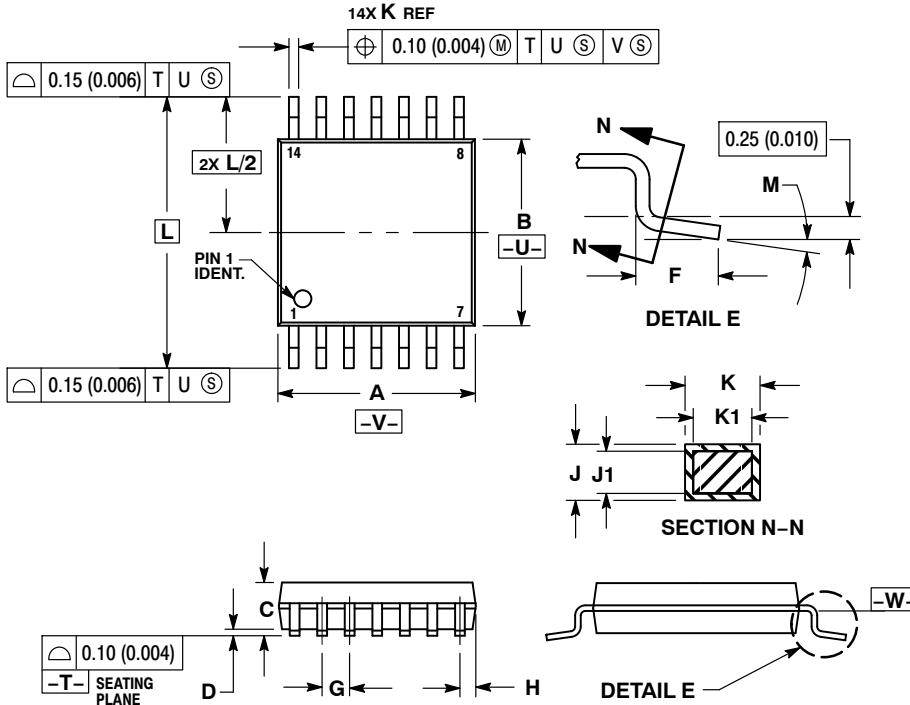
DIMENSIONS: MILLIMETERS

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

TSSOP-14
DT SUFFIX
CASE 948G-01
ISSUE B

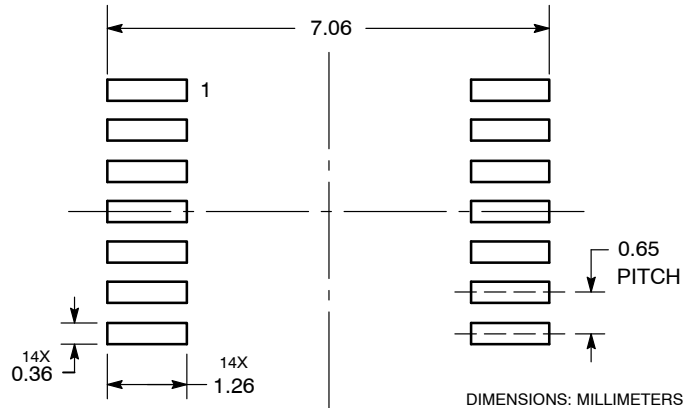


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE -W-.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4.90	5.10	0.193	0.200
B	4.30	4.50	0.169	0.177
C	---	1.20	---	0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65 BSC		0.026 BSC	
H	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40 BSC		0.252 BSC	
M	0°	8°	0°	8°

SOLDERING FOOTPRINT*

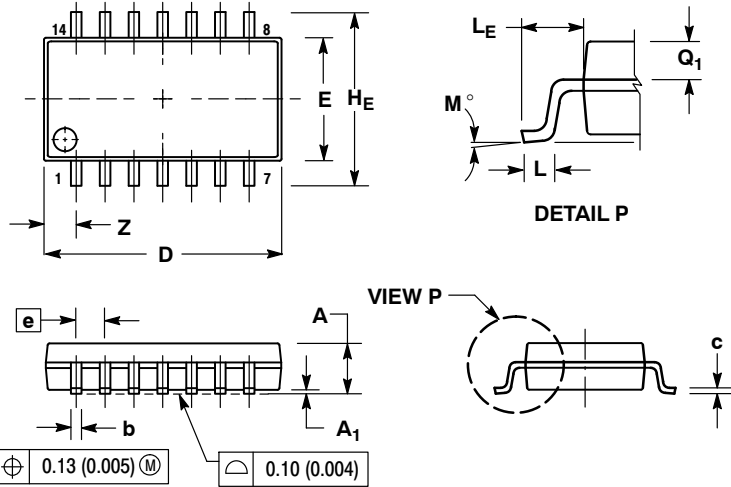


*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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PACKAGE DIMENSIONS

SOEIAJ-14 CASE 965-01 ISSUE B



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	---	2.05	---	0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.10	0.20	0.004	0.008
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
HE	7.40	8.20	0.291	0.323
L	0.50	0.85	0.020	0.033
LE	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q ₁	0.70	0.90	0.028	0.035
Z	---	1.42	---	0.056

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